



Detectors for ¹⁶³Ho EC decay endpoint measurement



The length of the inductive section is much shorter than the wavelength at resonator frequency, ensuring uniform response.

The ¹⁶³Ho will be embedded in the inductive part of the resonator. 10¹² Ho nuclei are needed for a count rate of 10 Hz

The Ho needs to be deep enough to ensure low escape probability for 2 keV electrons.

But very thick films are difficult to grow





Nitrides with like TiN, TaN and HfN, will be investigated A thickness of $\implies 0.5\mu m$ can be enough

The fundamental noise of a pair-breaking detector for phonon counting applications is set by the statistics of the energy cascade process that produces quasi-particles and low energy phonons:

 $N_{ab} = \eta h v / \Delta \sim \eta h v / (1.75 k_B T_c)$

Considering a sensor material with $T_c = 4.6K$, and assuming a typical conversion efficiency of 0.6, for a 2 keV decay event $N_{qp} \approx 1.7 \cdot 10^6$ guasi particles are produced; we expect then a theoretical resolution

 $\Delta E_{th} = 2 keV / N_{op}^{1/2} = 1.5 eV$

Considering also the Fano factor (F < 1), the theoretical energy resolution will be slightly better.

Stoichiometric nitrides metals have a high T is recombination time becomes too short, increasing the recombination noise: $(N_{ab}/\tau_R)\Delta^2$

Sub-stoichiometric materials, with lower T_c , are considered

Resonances can be fitted by the analytical formula:



Jiansong Gao, Fitting the resonance data from network analyzer, 2005, (unpublished manuscript)

For our resonators, we obtained Q = $7 \cdot 10^4 \div 10^5$ and Q_c = $10^5 \div 10^6$. Consequently, since Q⁻¹=Q_c⁻¹+Q_i⁻¹, Q_i = $2 \cdot 10^5 \div 4 \cdot 10^5$

Sweeping the temperature from 30mK up to ~1K it is possible to extract the gap parameter. For TiN a gap parameter of 0.7 meV has been measured, wich, accordingly to the BCS theroy, means $T_c \sim 4.6$ K.

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